

Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of the claims in the application:

Listing of Claims:

1. (currently amended) A method for making a semiconductor device comprising:
forming a conductive path on a substrate, the conductive path made of copper;
removing an oxide from the conductive path by etching the conductive path with a medium having a mildly acidic or mildly basic solution;
depositing a metal more noble than copper on the conductive path, from an aqueous solution by immersion plating;
facilitating a diffusion of the metal more noble than copper into the conductive path, the metal more noble than copper having a low solubility to substantially diffuse into grain boundaries of the conductive path to significantly increase reliability of the conductive path; and
planarizing the conductive path after the facilitating to remove the deposited metal and a portion of the conductive path.
2. (previously presented) The method of claim 1, wherein the metal more noble than copper comprises platinum.
3. (previously presented) The method of claim 1, wherein the metal more noble than copper comprise rhodium.
4. (previously presented) The method of claim 1, wherein forming the conductive path comprises a damascene process.
5. (previously presented) The method of claim 1, wherein the metal more noble than copper comprises gold.
6. (cancelled)

7. (previously presented) The method of claim 1, wherein the metal more noble than copper comprises ruthenium.
8. (previously presented) The method of claim 1, wherein the metal more noble than copper comprises osmium.
9. (cancelled)
10. (previously presented) The method of claim 11, wherein the metal more noble than copper comprises iridium.
11. (cancelled)
12. (currently amended) The method of claim 1, wherein depositing the metal more noble than copper comprises ~~removing an oxide from the conductive path, and~~ immersing the conductive path in an aqueous solution having at least the ~~second material~~ metal more noble than copper.
13. (cancelled)
14. (cancelled)
15. (currently amended) The method of claim 1, wherein facilitating diffusion of the ~~second material~~ metal more noble than copper comprises heat treating the conductive path having the deposited metal more noble than copper.
16. (previously presented) The method of claim 15, wherein heat treating the conductive path comprises annealing the conductive path to substantially diffuse the metal more noble than copper to the grain boundaries within the copper, the temperature and time based at least in part on the copper and the metal more noble than copper.

17. (original) The method of claim 1, wherein the conductive path comprises at least of one of a conductive line and a conductive interconnect.

18-29. (cancelled)